

AMENDMENTS TO THE SPECIFICATION

Please amend the paragraph bridging pages 9 and 10 as follows:

In this event, the resist pattern 7a was slightly offset from the main opening 5 so that the etching mask layer 3a was exposed a little. Further, the shape of the resist pattern 7a was degraded as the etching proceeded. ~~AS~~ As a consequence, the exposed portion of the etching mask layer 3a was enlarged and damage to the etching mask layer 3a was caused. However, there was no influence to the underlying light-shielding film 2.

Page 10, please replace full paragraph no. 2 with the following amended paragraph:

Next, the etching mask layer was removed by the use of an etchant containing ceric ammonium nitrate and perchloric acid and cleaning was carried out. Thus, an auxiliary pattern type phase shift mask as completed (Fig. 1, (7)).

Page 10, please replace full paragraph no. 5 with the following amended paragraph:

In the foregoing embodiment, the transparent substrate is recess-etched at the main opening. However, etching may be carried out at the auxiliary openings instead of at the main opening. It is noted here that the dimension of each auxiliary opening is so small that the etching at the main opening is preferable in view of the processing accuracy.